



PJD9P06A-AU

60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-7 A

Features

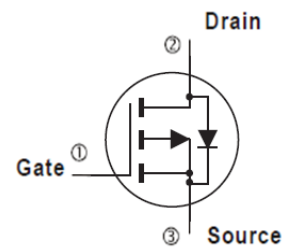
- $R_{DS(ON)}, V_{GS}@-10V, I_D@-3.5A < 170m\Omega$
- $R_{DS(ON)}, V_{GS}@-4.5V, I_D@-2A < 220m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 Standard

Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0104 ounces, 0.297grams



TO-252AA



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	+20	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	-7.0	A
	$T_C=100^\circ\text{C}$		-4.3	
Pulsed Drain Current (Note 1)	$T_C=25^\circ\text{C}$	I_{DM}	-28	
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	15.6	W
	$T_C=100^\circ\text{C}$		6.2	
Continuous Drain Current	$T_A=25^\circ\text{C}$	I_D	-2.5	A
	$T_A=70^\circ\text{C}$		-2.0	A
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	2.0	W
Power Dissipation	$T_A=70^\circ\text{C}$		1.3	
Single Pulse Avalanche Energy (Note 6)		E_{AS}	32	mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ\text{C}$
Typical Thermal resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	8	$^\circ\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$	62.5	

- Limited only By Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.88	-2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-3.5A$	-	150	170	m Ω
		$V_{GS}=-4.5V, I_D=-2A$	-	190	220	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V$	-	-	-1.0	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	$V_{DS}=-30V, I_D=-3A,$ $V_{GS}=-10V$ (Note 2,3)	-	8.3	-	nC
Gate-Source Charge	Q_{gs}		-	1.8	-	
Gate-Drain Charge	Q_{gd}		-	1.6	-	
Input Capacitance	C_{iss}	$V_{DS}=-30V, V_{GS}=0V,$ $f=1.0\text{MHz}$	-	430	-	pF
Output Capacitance	C_{oss}		-	33	-	
Reverse Transfer Capacitance	C_{rss}		-	29	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-30V, I_D=-1.0A,$ $V_{GS}=-10V, R_G=6\Omega$ (Note 2,3)	-	5.1	-	ns
Turn-On Rise Time	t_r		-	20	-	
Turn-Off Delay Time	$t_{d(off)}$		-	36	-	
Turn-Off Fall Time	t_f		-	11	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	-7	A
Reverse Recovery Time	V_{SD}	$I_S=-1A, V_{GS}=0V$	-	-0.76	-1.0	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics
3. Repetitive rating, pulse width limited by junction temperature $T_J(\text{MAX})=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.
4. The maximum current rating is package limited
5. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz. square pad of copper
6. $L=1\text{mH}, I_{AS}=-8A, V_{GS}=-10V, V_{DS}=-25V, R_G=25\text{ohm}$
7. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

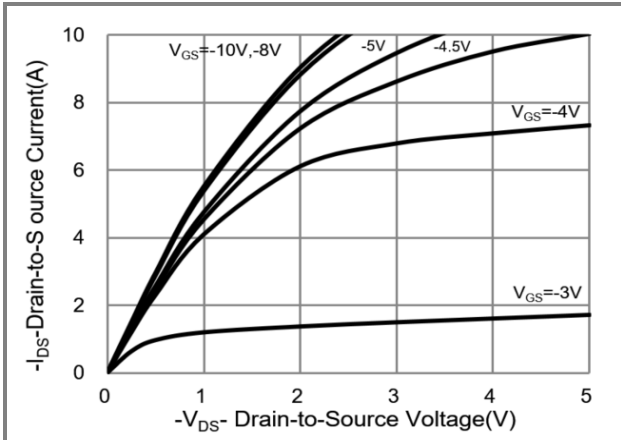


Fig.1 On-Region Characteristics

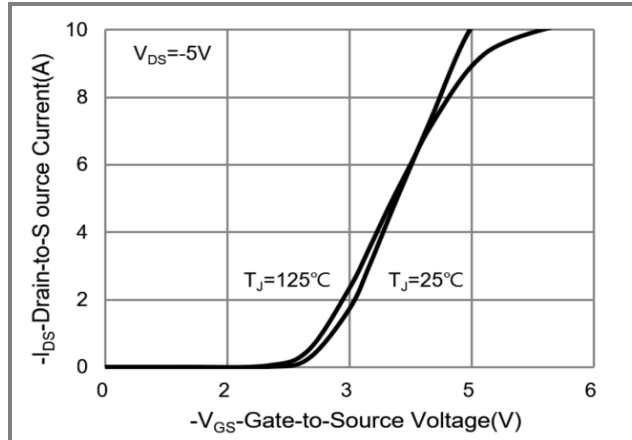


Fig.2 Transfer Characteristics

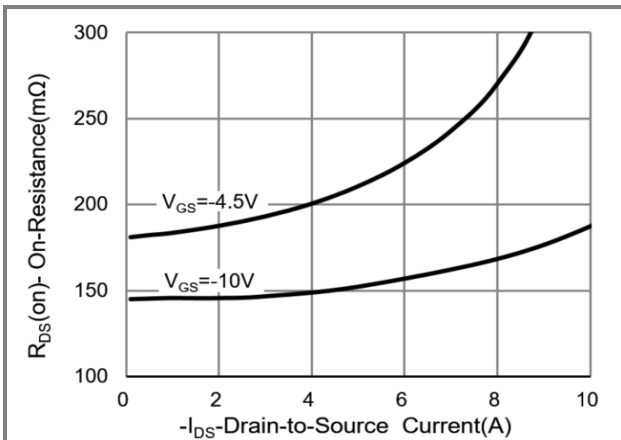


Fig.3 On-Resistance vs. Drain Current

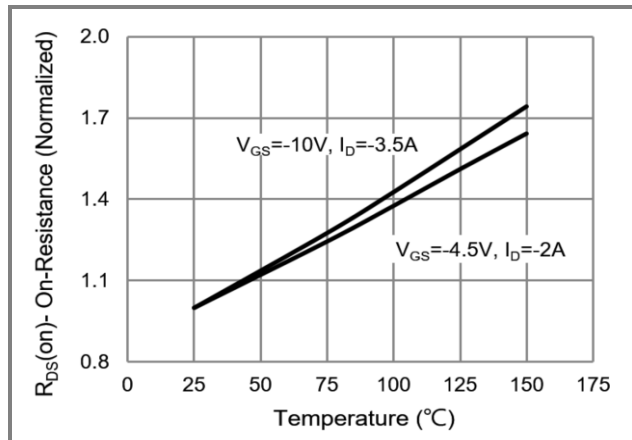


Fig.4 On-Resistance vs. Junction temperature

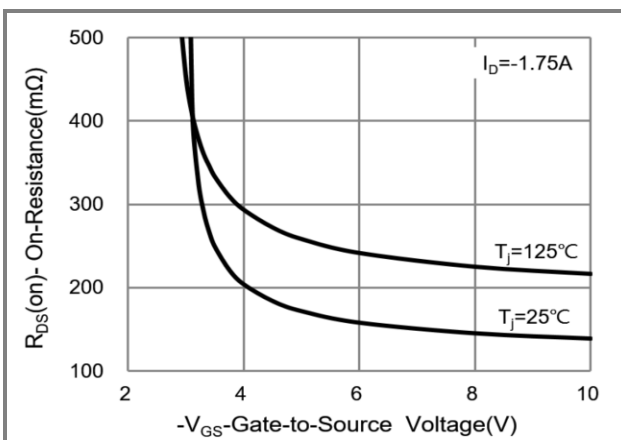


Fig.5 On-Resistance Variation with V_GS.

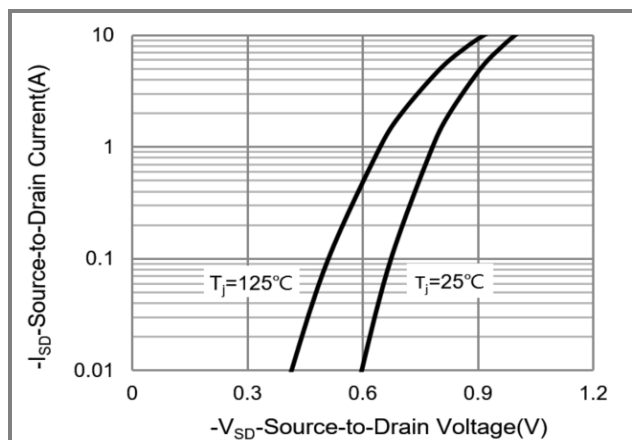


Fig.6 Body Diode Characteristics



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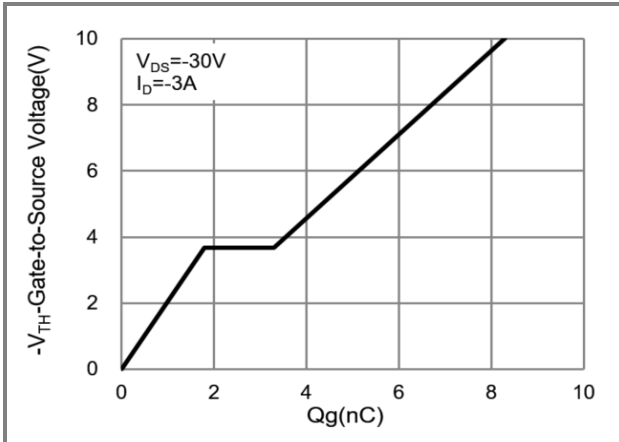


Fig.7 Gate-Charge Characteristics

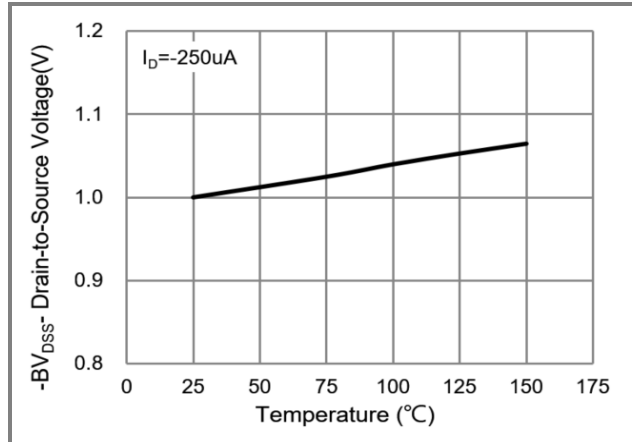


Fig.8 Breakdown Voltage Variation vs. Temperature

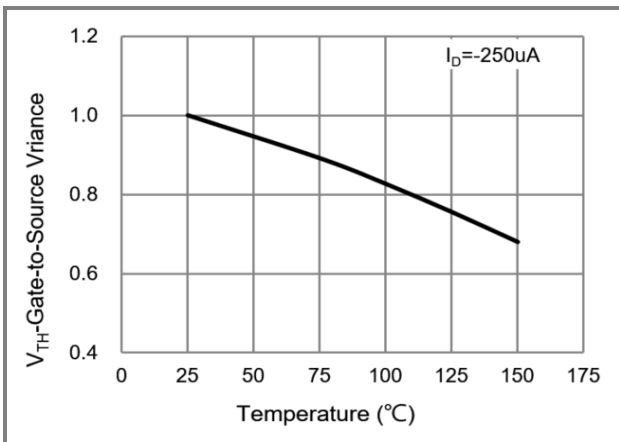


Fig.9 Threshold Voltage Variation with Temperature.

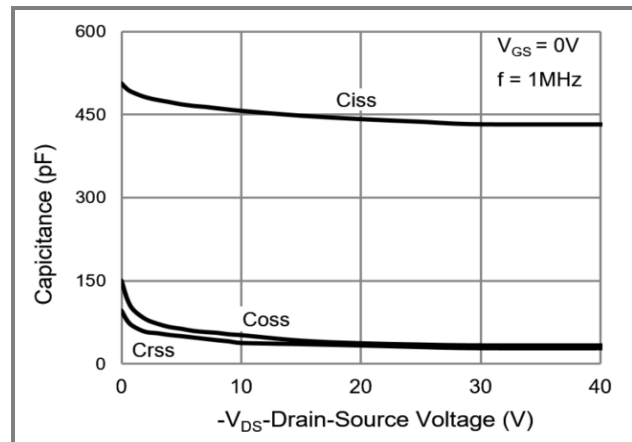


Fig.10 Capacitance vs. Drain-Source Voltage.

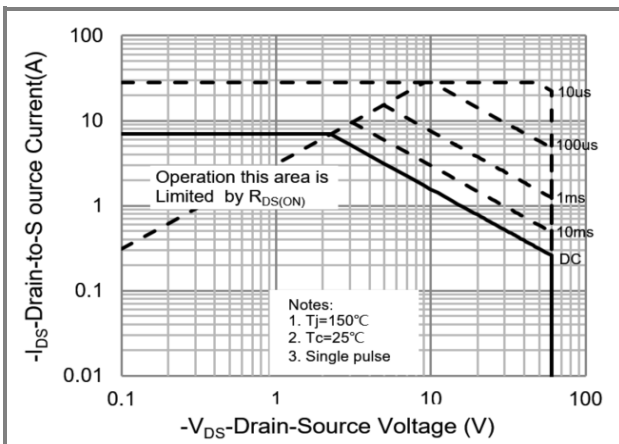


Fig.11 Maximum Safe Operating Area



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TYPICAL CHARACTERISTIC CURVES

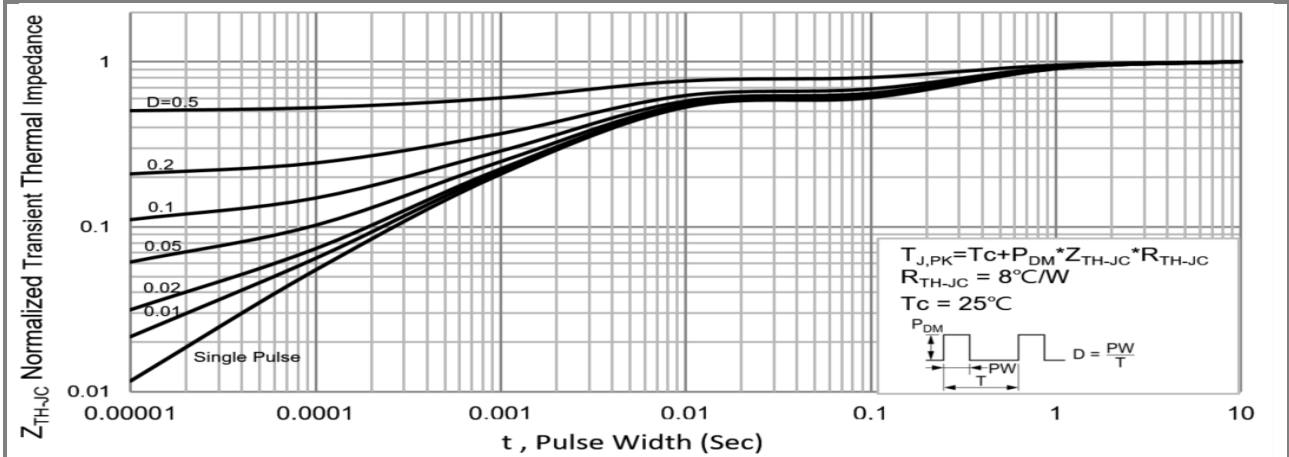


Fig.12 Normalized Thermal Transient Impedance



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Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD9P06A-AU_L2_000A1	TO-252AA	3,000pcs / 13" reel	D9P06A	Halogen free

Packaging Information & Mounting Pad Layout

